



PCN Number:	20230620000.2		PCN Date:	June 20, 2023	
Title:	Qualification of LFAB as an additional Wafer Fab site option for select devices				
Customer Contact:	Change Management team		Dept:	Quality Services	
Proposed 1st Ship Date:	Dec 20, 2023		Sample Requests accepted until:	July 20, 2023*	
*Sample requests received after July 20, 2023 will not be supported.					
Change Type:					
<input type="checkbox"/>	Assembly Site	<input type="checkbox"/>	Design	<input type="checkbox"/>	Wafer Bump Material
<input type="checkbox"/>	Assembly Process	<input type="checkbox"/>	Data Sheet	<input type="checkbox"/>	Wafer Bump Process
<input type="checkbox"/>	Assembly Materials	<input type="checkbox"/>	Part number change	<input checked="" type="checkbox"/>	Wafer Fab Site
<input type="checkbox"/>	Mechanical Specification	<input type="checkbox"/>	Test Site	<input type="checkbox"/>	Wafer Fab Material
<input type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process	<input type="checkbox"/>	Wafer Fab Process
PCN Details					
Description of Change:					
Texas Instruments is pleased to announce the addition of LFAB as an additional Wafer Fab site option for the products listed in the "Product Affected" section of this document.					
Current Fab Site			Additional Fab Site		
Current Fab Site	Process	Wafer Diameter	New Fab Site	Process	Wafer Diameter
TSMC-F14	F021	300mm	LFAB	F65	300mm
DMOS6	F65	300mm			
UMC12i	F65	300mm			
Qual details are provided in the Qual Data Section.					
Reason for Change:					
Continuity of supply					
Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):					
None					
Changes to product identification resulting from this PCN:					
Device Symbol: <div style="display: flex; align-items: flex-start; margin-top: 10px;"> <div style="flex: 1; text-align: center;">  <p>TMS320 F28379DPTPT \$\$-YMLLLLS <u>G4</u></p> </div> <div style="flex: 2; margin-left: 20px;"> <p>YMLLLLS = Lot Trace Code</p> <p>YM = 2-Digit Year/Month Code</p> <p>LLLL = Assembly Lot</p> <p>S = Assembly Site Code</p> <p>\$\$ = Wafer Fab Code as applicable</p> <p># = Silicon Revision Code</p> <p><u>G4</u> = Green (Low Halogen and RoHS-compliant)</p> </div> </div> <div style="margin-top: 10px;">  </div>					
Original Fab Field: \$\$ = YF → TSMC-F14 Or \$\$ = \$7 → UMC 12i Or \$\$ = \$4 → DMOS6					
Updated Fab Field: \$\$ = 3L → LFAB					

Current Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
TSMC-F14	T14	TWN	Tainan City
DMOS6	DM6	USA	Dallas
UMC12i	UMI	SGP	Singapore

Additional Fab Site Information:

New Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
LFAB	LHI	USA	Lehi

Sample product shipping label (not actual product label)

**Product Affected:**

TMS320F28075PTPQ	TMS320F28375SPZPQR	TMS320F28377SPTPQ	TMS320F28379DZWTQR
TMS320F28075PTPQR	TMS320F28377DPTPQ	TMS320F28377SPZPQ	
TMS320F28075PZPQ	TMS320F28377DZWTQ	TMS320F28377SZWTQ	
TMS320F28375SPZPQ	TMS320F28377DZWTQR	TMS320F28379DPTPQ	

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TMS320F28379SPTPQ	Qual Device: TMS320F28379SZWTQR
Test Group A - Accelerated Environment Stress Tests									
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL3 260C	-	3/693/0	
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	110C/85%RH	264 Hours	3/231/0	
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	3/231/0	
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	1/5/0	
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	3/135/0	
Test Group B - Accelerated Lifetime Simulation Tests									
HTOL	B1	JEDEC JESD22-A108	1	77	Life Test	125C	1000 Hours	3/231/0	-
ELFR	B2	AEC Q100-008	1	77	Early Life Failure Rate	125C	48 Hours	3/2400/0	-
EDR	B3	AEC Q100-005	1	77	NVM Endurance, Data Retention, and Op Life	125C NVM program cycling before B1 and B3	10 K cycles	3/462/0	-
Test Group C - Package Assembly Integrity Tests									

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TMS320F28379SPTPQ	Qual Device: TMS320F28379SZWTQR
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	1/15/0	
Test Group D - Die Fabrication Reliability Tests									
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDb	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests									
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	1/3/0	1/3/0
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	500 Volts	1/3/0	1/3/0
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100-004	-	1/6/0	
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	3/90/0	
Additional Tests									

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-CHG-2112-003

[1]-1 unit passed 25C (Q100 requirement) marginal failure at 125C. Appears to be tester repeatability and unrelated to stress test. Refer to QEM-EVAL-2211-00276

Q006 Qualification Summary

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: TMS320F28379SPTPQ
Test Group A - Accelerated Environment Stress Tests								
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL3 260C	1 Step	3/0/0
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	1 Step	3/66/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	1 Step	3/66/0
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	110C/85%RH	264 Hours	3/231/0
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	3/3/0
HAST	A2.1.3	-	3	30	Wire Bond Shear, post bHAST, 1X	Post stress	Wires	3/9/0
HAST	A2.1.4	-	3	30	Bond Pull over Stitch, post bHAST, 1X	Post stress	Wires	3/9/0
HAST	A2.1.5	-	3	30	Bond Pull over Ball, post bHAST, 1X	Post stress	Wires	3/9/0
HAST	A2.2	JEDEC JESD22-A110	3	77	Biased HAST	110C/85%RH	528 Hours	3/210/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	3/3/0
HAST	A2.2.3	-	3	30	Wire Bond Shear, post bHAST, 2X	Post stress	Wires	3/9/0
HAST	A2.2.4	-	3	30	Bond Pull over Stitch, post bHAST, 2X	Post stress	Wires	3/9/0
HAST	A2.2.5	-	3	30	Bond Pull over Ball, post bHAST, 2X	Post stress	Wires	3/9/0
TC	A4.1	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0
TC	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	3/66/0
TC	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	3/3/0
TC	A4.1.3	-	3	30	Wire Bond Shear, post TC, 1X	Post stress	Wires	3/9/0
TC	A4.1.4	-	3	30	Bond Pull over Stitch, post TC, 1X	Post stress	Wires	3/9/0
TC	A4.1.5	-	3	30	Bond Pull over Ball, post TC, 1X	Post stress	Wires	3/9/0
TC	A4.2	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	1000 Cycles	3/210/0
TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	3/66/0
TC	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	3/3/0
TC	A4.2.3	-	3	30	Wire Bond Shear, post TC, 2X	Post stress	Wires	3/9/0
TC	A4.2.4	-	3	30	Bond Pull over Stitch, post TC, 2X	Post stress	Wires	3/9/0
TC	A4.2.5	-	3	30	Bond Pull over Ball, post TC, 2X	Post stress	Wires	3/9/0
HTSL	A6.1	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	1000 Hours	3/135/0
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	3/3/0
HTSL	A6.2	JEDEC JESD22-A103	3	45	High Temperature Storage Life	150C	2000 Hours	3/132/0
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	3/3/0

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- Room : AC/HAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

ZVEI IDs: SEM-PW-13

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.

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